

## 2N681 thru 2N689 (SILICON)



CASE 263

Industrial-type, silicon controlled rectifiers in a stud package with current handling capability to 25 amperes at junction temperatures to 125°C. MCR equivalents available in TO-48 package – i.e. – 2N681 available in TO-48 package as MCR681.

### MAXIMUM RATINGS ( $T_J = 125^\circ\text{C}$ unless otherwise noted)

Rating	Symbol	Value	Unit
Peak Reverse Blocking Voltage* †	$V_{RSM(rep)}^{*†}$	25	Volts
2N681		50	
2N682		100	
2N683		150	
2N684		200	
2N685		250	
2N686		300	
2N687		400	
2N688		500	
2N689	500		
Peak Reverse Blocking Voltage* (Transient) (non-recurrent $t = 5$ ms max.)	$V_{RSM(non-rep)}^*$	35	Volts
2N681		75	
2N682		150	
2N683		225	
2N684		300	
2N685		350	
2N686		400	
2N687		500	
2N688		600	
2N689	600		
Forward Current RMS (all conduction angles)	$I_T$	25	Amp
Peak Forward Surge Current (One cycle, 60 Hz, $T_J = -65$ to $+125^\circ\text{C}$ )	$T_{TSM}$	200	Amp
Circuit Fusing Considerations ( $T_J = -65$ to $+125^\circ\text{C}$ , $t \leq 8.3$ ms)	$I^2t$	165	$\text{A}^2\text{s}$
Peak Gate Power-Forward	$P_{GM}$	5.0	Watts
Average Gate Power-Forward	$P_{G(AV)}$	0.5	Watt
Peak Gate Current-Forward	$I_{GM}$	2.0	Amp
Peak Gate Voltage-Forward	$V_{GFM}$	10	Volts
Reverse	$V_{GRM}$	5.0	
Operating Junction Temperature Range	$T_J$	-65 to +125	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	-65 to +150	$^\circ\text{C}$
Stud Torque	—	30	in. lb.

†  $V_{RSM}$  for all types can be applied on a continuous dc basis without incurring change.

\*  $V_{RSM(rep)}$  ratings apply for zero or negative gate voltage.

**2N681 thru 2N689 (continued)**
**ELECTRICAL CHARACTERISTICS (T<sub>c</sub> = 25°C unless otherwise noted)**

Characteristic	Symbol	Min	Typ	Max	Units
Peak Forward Blocking Voltage (T <sub>J</sub> = 125°C)	V <sub>DRM</sub>				Volts
2N681		25	—	—	
2N682		50	—	—	
2N683		100	—	—	
2N684		150	—	—	
2N685		200	—	—	
2N686		250	—	—	
2N687		300	—	—	
2N688		400	—	—	
2N689		500	—	—	
Peak Forward or Reverse Blocking Current (T <sub>J</sub> = 125°C)	I <sub>DRM</sub> I <sub>RDM</sub>				mA
2N681 - 2N684		—	—	10.0	
2N685		—	—	10.0	
2N686		—	—	10.0	
2N687		—	—	10.0	
2N688		—	—	8.0	
2N689		—	—	6.0	
Gate Trigger Current (Continuous dc) (Anode Voltage = 7 Vdc, R <sub>L</sub> = 50 Ω)	I <sub>GT</sub>	—	10	25	mA
Gate Trigger Voltage (Continuous dc) (Anode Voltage = 7 Vdc, R <sub>L</sub> = 50 Ω)	V <sub>GT</sub>	0.25	—	3.0	Volts
Holding Current (Anode Voltage = 7 Vdc, Gate Open)	I <sub>H</sub>	—	20	—	mA
Forward On Voltage (I <sub>T</sub> = 20 Adc)	V <sub>TM</sub>	—	1.1	1.5	Volts
Turn-On Time (I <sub>T</sub> = 10A, I <sub>G</sub> = 200 mA)	t <sub>gt</sub>	—	1.0	—	μs
Turn-Off Time (I <sub>T</sub> = 10 A; I <sub>R</sub> = 10 A, dv/dt = 30 V/μs min, T <sub>J</sub> = 125°C) (V <sub>DRM</sub> = rated voltage)	t <sub>q</sub>	—	30	—	μs
Forward Voltage Application Rate (Gate open, T <sub>J</sub> = 125°C)	dv/dt	—	30	—	V/μs
Thermal Resistance (Junction to Case)	θ <sub>JC</sub>	—	1.0	2.0	°C/W

# 2N681 thru 2N689 (continued)

